

Product Overview

CNY17F2M: 6-Pin DIP High BV_{CEO} Phototransistor Output Optocoupler

For complete documentation, see the data sheet.

The CNY17XM, CNY17FXM and MOC810XM devices consist of a gallium arsenide infrared emitting diode coupled with an NPN phototransistor in a dual in-line package.

Features

- High BV_{CEO} : 70 V Minimum (CNY17XM, CNY17FXM, MOC8106M)
- Closely Matched Current Transfer Ratio (CTR)
- Minimizes Unit-to-Unit Variation
- Current Transfer Ratio In Select Groups
- Very Low Coupled Capacitance Along With No Chip-to-Pin 6 Base Connection for Minimum Noise Susceptability (CNY17FXM, MOC8106M)
- Safety and Regulatory Approvals:
 - UL1577, 4,170 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

Applications

- AC-DC Merchant Power Supply
- Consumer Appliances
- Industrial Motor

Part Electrical Specifications

Product	Compliance	Status	Channels	CTR (Min) (%)	CTR (Max) (%)	CTR tested @ IF (mA)	$V_{CE(sat)}$ (Max) (V)	BV_{CEO} (Min) (V)	BV_{CB} (Min) (V)	BV_{EC} (Min) (V)	t_{on} (Max) (μ s)	t_{off} (Max) (μ s)	V_{ISO} (Min) (V)	T_{OPR} (Min) ($^{\circ}$ C)	T_{OPR} (Max) ($^{\circ}$ C)	Package Type
CNY17F2M	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2SM	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2SR2M	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2SR2VM	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2SVM	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2TVM	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6
CNY17F2VM	Pb-free	Active	1	63	125	10	0.4	70	70	7	2	3	4200	-40	100	PDIP-6

For more information please contact your local sales support at www.onsemi.com.

Created on: 5/26/2019